KATERINA TSAGARAKI
CURRICULUM VITAE

PERSONAL DATA

Birth:	19 July 1965, Rethymno, Greece
Nationality:	Hellenic
Marital status:	Married, 2 children
Work Address:	Microelectronics Research Group Institute of Electronic Structure and Lasers Foundation for Research and Technology-Hellas P.O.Box 1385 70013 Heraklion Crete, Greece
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EDUCATION AND WORK EXPERIENCE

Sept. 1983 - July 1987	B.Sc. in Physics, Department of Physics, University of Crete Thesis: "EDXS microanalysis on semiconductors" Scholarships from the "State Scholarship Foundation".
Sept. 1987 – May 1988	Research assistant at Department of Physics, Kansas State University, Manhattan Kansas, USA. Training and work in synthesis and characterization of magnetic materials.
July 1988 - Today	Technical Research staff at I.E.S.L. (Institute of Electronic Structure and Laser) (M.R.G., Microelectronics Research Group), F.O.R.T.H. (Foundation of Research and Technology Hellas). Responsible for the morphological and structural characterization of MBE grown compound semiconductors.
1990 - Today	Participation in more than 30 National and European funded research projects such as GA no 214610 (MORGAN), FP7-ICT-2011-7 GA 288531 (NANOTEC), Co. no NMP4-CT-2003-505641 (GANANO), ΑΡΙΣΤΕΙΑ ΚΩΔ.1935 (NITROHEMT), THALIS/UoC (NanoWire).
1990 - Today	Training of undergraduate, master and PhD students (University of Crete) to methods and techniques for morphological and structural study of materials.

LANGUAGES

Greek:	Mother tongue
English:	Fluently spoken and written
French:	Basic knowledge

RESEARCH EXPERIENCE

Study of various novel semiconducting materials such as III-nitrides / SiC / GaAs, nano-heterostructures (nanowires, quantum wells, quantum dots) and electronic devices, utilizing the following techniques:

High Resolution X-ray Diffraction

Structural characterization of single crystalline semiconductors.
Determination of lattice parameters, crystal quality, crystal strain, compound concentration, crystal defects density, crystal orientation issues. Reciprocal Space Mapping of the crystal.

Atomic Force Microscopy, Scanning Tunneling Microscopy

Morphology and properties of semiconductors' surfaces in atomic scale.
Contact and Tapping mode.

Field Emission Scanning Electron Microscopy

High Resolution Electron Imaging of semiconductors' topography in planar and cross section view.
Study of the doping/implantation profile by the Secondary Electron Potential Contrast.

Conventional Transmission Electron Microscopy

Planar-view and cross-sectional imaging of inner structure of single crystalline semiconductors. Electron Diffraction techniques.

Energy Dispersive X-ray Spectroscopy

Qualitative & Quantitative Elemental Microanalysis.

BIBLIOMETRICS

Documents:	93
Patents:	1 Greek Patent, No 1008013
Citations:	1187
h-index:	18
Data updated on:	15th December 2018